

# Alex Hamilton

## List of Publications by Citations

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202  
papers

4,400  
citations

34  
h-index

58  
g-index

242  
ext. papers

5,101  
ext. citations

4.7  
avg, IF

5.16  
L-index

#	Paper	IF	Citations
202	Charge-based quantum computing using single donors in semiconductors. <i>Physical Review B</i> , <b>2004</b> , 69,	3.3	237
201	Metal-Insulator Transition at B=0 in a Dilute Two Dimensional GaAs-AlGaAs Hole Gas. <i>Physical Review Letters</i> , <b>1998</b> , 80, 1292-1295	7.4	219
200	Coherent electronic transfer in quantum dot systems using adiabatic passage. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	218
199	Density-dependent spin polarization in ultra-low-disorder quantum wires. <i>Physical Review Letters</i> , <b>2002</b> , 89, 246801	7.4	142
198	Many-body spin-related phenomena in ultra low-disorder quantum wires. <i>Physical Review B</i> , <b>2001</b> , 63,	3.3	135
197	High-temperature superfluidity in double-bilayer graphene. <i>Physical Review Letters</i> , <b>2013</b> , 110, 146803	7.4	131
196	Zero-Energy Modes from Coalescing Andreev States in a Two-Dimensional Semiconductor-Superconductor Hybrid Platform. <i>Physical Review Letters</i> , <b>2017</b> , 119, 176805	7.4	129
195	Toward Atomic-Scale Device Fabrication in Silicon Using Scanning Probe Microscopy. <i>Nano Letters</i> , <b>2004</b> , 4, 1969-1973	11.5	128
194	Velocity-modulation control of electron-wave propagation in graphene. <i>Physical Review B</i> , <b>2010</b> , 81,	3.3	95
193	Weak localization, hole-hole interactions, and the "Metal"-insulator transition in two dimensions. <i>Physical Review Letters</i> , <b>2000</b> , 84, 2489-92	7.4	90
192	Realization of atomically controlled dopant devices in silicon. <i>Small</i> , <b>2007</b> , 3, 563-7	11	87
191	Encapsulation of phosphorus dopants in silicon for the fabrication of a quantum computer. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 3197-3199	3.4	83
190	Zeeman splitting in ballistic hole quantum wires. <i>Physical Review Letters</i> , <b>2006</b> , 97, 026403	7.4	75
189	Electrically detected magnetic resonance in ion-implanted Si:P nanostructures. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 182115	3.4	73
188	A room-temperature ferroelectric semimetal. <i>Science Advances</i> , <b>2019</b> , 5, eaax5080	14.3	68
187	Reentrant Insulator-Metal-Insulator Transition at B=0 in a Two-Dimensional Hole Gas. <i>Physical Review Letters</i> , <b>1999</b> , 82, 1542-1545	7.4	58
186	Antisymmetric magnetoresistance in van der Waals FeGeTe/graphite/FeGeTe trilayer heterostructures. <i>Science Advances</i> , <b>2019</b> , 5, eaaw0409	14.3	57

185	Magnetization Instability in a Two-Dimensional System. <i>Physical Review Letters</i> , <b>1997</b> , 79, 4449-4452	7.4	49
184	Maximizing the Hilbert space for a finite number of distinguishable quantum states. <i>Physical Review Letters</i> , <b>2004</b> , 92, 097901	7.4	49
183	Progress in silicon-based quantum computing. <i>Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences</i> , <b>2003</b> , 361, 1451-71	3	49
182	Pauli Spin Blockade of Heavy Holes in a Silicon Double Quantum Dot. <i>Nano Letters</i> , <b>2015</b> , 15, 7314-8	11.5	48
181	Ballistic transport in induced one-dimensional hole systems. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 092105	3.4	46
180	Weak localization in high-quality two-dimensional systems. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	46
179	Influence of doping density on electronic transport in degenerate Si:P Doped layers. <i>Physical Review B</i> , <b>2006</b> , 73,	3.3	45
178	Enhanced g factors of a one-dimensional hole gas with quantized conductance. <i>Physical Review B</i> , <b>1997</b> , 55, R13409-R13412	3.3	44
177	Excitonic superfluidity and screening in electron-hole bilayer systems. <i>Physical Review B</i> , <b>2014</b> , 89,	3.3	42
176	Scanning probe microscopy for silicon device fabrication. <i>Molecular Simulation</i> , <b>2005</b> , 31, 505-515	2	42
175	Effect of encapsulation temperature on Si:P Doped layers. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 4953-4955	3.4	39
174	Frictional drag between parallel two-dimensional electron gases in a perpendicular magnetic field. <i>Journal of Physics Condensed Matter</i> , <b>1996</b> , 8, L557-L562	1.8	38
173	Conductance quantization and the $0.7e^2/h$ conductance anomaly in one-dimensional hole systems. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 012107	3.4	37
172	Strong and Tunable Spin-Orbit Coupling in a Two-Dimensional Hole Gas in Ionic-Liquid Gated Diamond Devices. <i>Nano Letters</i> , <b>2016</b> , 16, 3768-73	11.5	36
171	Impact of long- and short-range disorder on the metallic behaviour of two-dimensional systems. <i>Nature Physics</i> , <b>2008</b> , 4, 55-59	16.2	35
170	Electron-electron interactions in highly disordered two-dimensional systems. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	35
169	Spin-orbit interaction in a two-dimensional hole gas at the surface of hydrogenated diamond. <i>Nano Letters</i> , <b>2015</b> , 15, 16-20	11.5	34
168	Role of background impurities in the single-particle relaxation lifetime of a two-dimensional electron gas. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	32

167	One-dimensional conduction properties of highly phosphorus-doped planar nanowires patterned by scanning probe microscopy. <i>Physical Review B</i> , <b>2007</b> , 76,	3.3	32
166	Fabrication and characterization of ambipolar devices on an undoped AlGaAs/GaAs heterostructure. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 052101	3.4	30
165	Back-gated split-gate transistor: A one-dimensional ballistic channel with variable Fermi energy. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 2782-2784	3.4	30
164	Anisotropic Pauli Spin Blockade of Holes in a GaAs Double Quantum Dot. <i>Nano Letters</i> , <b>2016</b> , 16, 7685-7689	3.5	30
163	Spin-orbit interactions in inversion-asymmetric two-dimensional hole systems: A variational analysis. <i>Physical Review B</i> , <b>2017</b> , 95,	3.3	29
162	Correlated charge detection for readout of a solid-state quantum computer. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 577-579	3.4	29
161	Electronic properties of atomically abrupt tunnel junctions in silicon. <i>Physical Review B</i> , <b>2007</b> , 75,	3.3	28
160	Single-shot readout with the radio-frequency single-electron transistor in the presence of charge noise. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 143117	3.4	27
159	Metallic behavior in dilute two-dimensional hole systems. <i>Physical Review Letters</i> , <b>2001</b> , 87, 126802	7.4	27
158	Fractional quantum Hall effect in bilayer two-dimensional hole-gas systems. <i>Physical Review B</i> , <b>1996</b> , 54, R5259-R5262	3.3	27
157	Spin and orbital structure of the first six holes in a silicon metal-oxide-semiconductor quantum dot. <i>Nature Communications</i> , <b>2018</b> , 9, 3255	17.4	26
156	0.7 Structure and zero bias anomaly in ballistic hole quantum wires. <i>Physical Review Letters</i> , <b>2008</b> , 100, 016403	7.4	26
155	Probing the spin states of a single acceptor atom. <i>Nano Letters</i> , <b>2014</b> , 14, 1492-6	11.5	25
154	Observation of orientation- and k-dependent Zeeman spin-splitting in hole quantum wires on (100)-oriented AlGaAs/GaAs heterostructures. <i>New Journal of Physics</i> , <b>2010</b> , 12, 033043	2.9	25
153	Atomic-scale silicon device fabrication. <i>International Journal of Nanotechnology</i> , <b>2008</b> , 5, 352	1.5	25
152	Fabrication of induced two-dimensional hole systems on (311)A GaAs. <i>Journal of Applied Physics</i> , <b>2006</b> , 99, 023707	2.5	25
151	Impact of small-angle scattering on ballistic transport in quantum dots. <i>Physical Review Letters</i> , <b>2012</b> , 108, 196807	7.4	24
150	Resistively detected nuclear magnetic resonance in n- and p-type GaAs quantum point contacts. <i>Nano Letters</i> , <b>2011</b> , 11, 3147-50	11.5	24

149	Fabrication of high mobility in situ back-gated (311)A hole gas heterojunctions. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 2750-2752	3-4	24
148	Controlled single electron transfer between Si:P dots. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 192101	3-4	24
147	Transport in disordered monolayer MoS2 nanoflakes--evidence for inhomogeneous charge transport. <i>Nanotechnology</i> , <b>2014</b> , 25, 375201	3-4	23
146	Observation of the Kondo effect in a spin-3/2 hole quantum dot. <i>Physical Review Letters</i> , <b>2011</b> , 107, 076805	3-4	23
145	Narrow, highly P-doped, planar wires in silicon created by scanning probe microscopy. <i>Nanotechnology</i> , <b>2007</b> , 18, 044023	3-4	23
144	The use of etched registration markers to make four-terminal electrical contacts to STM-patterned nanostructures. <i>Nanotechnology</i> , <b>2005</b> , 16, 2446-9	3-4	23
143	Enhanced Zeeman splitting in Ga <sub>0.25</sub> In <sub>0.75</sub> As quantum point contacts. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 012105	3-4	22
142	Spin blockade in hole quantum dots: Tuning exchange electrically and probing Zeeman interactions. <i>Physical Review B</i> , <b>2017</b> , 95,	3-3	21
141	Using a tunable quantum wire to measure the large out-of-plane spin splitting of quasi two-dimensional holes in a GaAs nanostructure. <i>Nano Letters</i> , <b>2013</b> , 13, 148-52	11-5	21
140	Single hole transport in a silicon metal-oxide-semiconductor quantum dot. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 163508	3-4	20
139	AlGaAs/GaAs single electron transistor fabricated without modulation doping. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 112104	3-4	20
138	Fabrication and characterization of an induced GaAs single hole transistor. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 092103	3-4	20
137	The interplay between one-dimensional confinement and two-dimensional crystallographic anisotropy effects in ballistic hole quantum wires. <i>New Journal of Physics</i> , <b>2009</b> , 11, 043018	2-9	20
136	Observing sub-microsecond telegraph noise with the radio frequency single electron transistor. <i>Journal of Applied Physics</i> , <b>2004</b> , 96, 6827-6830	2-5	20
135	Electrical readout of a spin qubit without double occupancy. <i>Physical Review B</i> , <b>2005</b> , 71,	3-3	20
134	Bottom-up assembly of metallic germanium. <i>Scientific Reports</i> , <b>2015</b> , 5, 12948	4-9	18
133	Extreme sensitivity of the spin-splitting and 0.7 anomaly to confining potential in one-dimensional nanoelectronic devices. <i>Nano Letters</i> , <b>2012</b> , 12, 4495-502	11-5	18
132	Influence of surface states on quantum and transport lifetimes in high-quality undoped heterostructures. <i>Physical Review B</i> , <b>2013</b> , 87,	3-3	17

131	Stacking of 2D electron gases in Ge probed at the atomic level and its correlation to low-temperature magnetotransport. <i>Nano Letters</i> , <b>2012</b> , 12, 4953-9	11.5	17
130	Field-orientation dependence of the Zeeman spin splitting in (In,Ga)As quantum point contacts. <i>Physical Review B</i> , <b>2010</b> , 81,	3.3	17
129	Piezoelectric rotator for studying quantum effects in semiconductor nanostructures at high magnetic fields and low temperatures. <i>Review of Scientific Instruments</i> , <b>2010</b> , 81, 113905	1.7	17
128	Electrical Characterization of Ordered Si:P Dopant Arrays. <i>IEEE Nanotechnology Magazine</i> , <b>2007</b> , 6, 213-217	2.7	16
127	G-factor and well width variations for the two-dimensional hole gas in surface conducting diamond. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 042102	3.4	15
126	Thickness-dependent electronic structure in WTe <sub>2</sub> thin films. <i>Physical Review B</i> , <b>2018</b> , 98,	3.3	15
125	Development and operation of the twin radio frequency single electron transistor for cross-correlated charge detection. <i>Journal of Applied Physics</i> , <b>2004</b> , 96, 4508-4513	2.5	15
124	Electrical Control of the Zeeman Spin Splitting in Two-Dimensional Hole Systems. <i>Physical Review Letters</i> , <b>2018</b> , 121, 077701	7.4	14
123	Ultra-shallow quantum dots in an undoped GaAs/AlGaAs two-dimensional electron gas. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 103507	3.4	14
122	Effect of screening long-range Coulomb interactions on the metallic behavior in two-dimensional hole systems. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	14
121	Evolution of the bilayer $\nu=1$ quantum Hall state under charge imbalance. <i>Physical Review B</i> , <b>2005</b> , 71,	3.3	14
120	Strong Spin-Orbit Contribution to the Hall Coefficient of Two-Dimensional Hole Systems. <i>Physical Review Letters</i> , <b>2018</b> , 121, 087701	7.4	13
119	Confinement properties of a Ga <sub>0.25</sub> In <sub>0.75</sub> As/InP quantum point contact. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	13
118	Charge shelving and bias spectroscopy for the readout of a charge qubit on the basis of superposition states. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	13
117	Localisation and the metal-insulator transition in two dimensions. <i>Physica B: Condensed Matter</i> , <b>2001</b> , 296, 21-31	2.8	13
116	The electronic structure of a back-gated high electron mobility transistor. <i>Semiconductor Science and Technology</i> , <b>1991</b> , 6, 201-207	1.8	13
115	Quantum Anomalous Hall Effect in Magnetic Doped Topological Insulators and Ferromagnetic Spin-Gapless Semiconductors-A Perspective Review. <i>Small</i> , <b>2020</b> , 16, e1904322	11	13
114	Mechanisms for Strong Anisotropy of In-Plane g-Factors in Hole Based Quantum Point Contacts. <i>Physical Review Letters</i> , <b>2017</b> , 119, 116803	7.4	12

113	Detection and Control of Spin-Orbit Interactions in a GaAs Hole Quantum Point Contact. <i>Physical Review Letters</i> , <b>2017</b> , 118, 146801	7.4	12
112	Ground-plane screening of Coulomb interactions in two-dimensional systems: How effectively can one two-dimensional system screen interactions in another. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	12
111	Origin of gate hysteresis in p-type Si-doped AlGaAs/GaAs heterostructures. <i>Physical Review B</i> , <b>2012</b> , 86,	3.3	12
110	Donor activation and damage in Si $\beta$ O <sub>2</sub> from low-dose, low-energy ion implantation studied via electrical transport in MOSFETs. <i>Semiconductor Science and Technology</i> , <b>2005</b> , 20, 363-368	1.8	12
109	Scaling of the Kondo zero-bias peak in a hole quantum dot at finite temperatures. <i>Physical Review B</i> , <b>2013</b> , 87,	3.3	11
108	Ohmic conduction of sub-10nm P-doped silicon nanowires at cryogenic temperatures. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 052101	3.4	11
107	Measurements of a composite fermion split-gate device. <i>Physical Review B</i> , <b>1996</b> , 53, R7596-R7598	3.3	11
106	. <i>IEEE Transactions on Information Theory</i> , <b>1993</b> , 39, 1043-1046	2.8	11
105	Manifestation of a non-Abelian Berry phase in a p-type semiconductor system. <i>Physical Review B</i> , <b>2016</b> , 93,	3.3	10
104	Is it the boundaries or disorder that dominates electron transport in semiconductor $\square$ billiardsR. <i>Fortschritte Der Physik</i> , <b>2013</b> , 61, 332-347	5.7	10
103	Compressibility measurements of quasi-one-dimensional quantum wires. <i>Physical Review Letters</i> , <b>2011</b> , 107, 126801	7.4	10
102	Radio-frequency reflectometry on large gated two-dimensional systems. <i>Review of Scientific Instruments</i> , <b>2008</b> , 79, 123901	1.7	10
101	Interaction correction to the longitudinal conductivity and Hall resistivity in high-quality two-dimensional GaAs electron and hole systems. <i>Physical Review B</i> , <b>2005</b> , 72,	3.3	10
100	Transition from one- to two-subband occupancy in the 2DEG of back-gated modulation-doped GaAs-Al <sub>x</sub> Ga <sub>1-x</sub> As heterostructures. <i>Physical Review B</i> , <b>1995</b> , 51, 17600-17604	3.3	10
99	Electrical control of the sign of the g factor in a GaAs hole quantum point contact. <i>Physical Review B</i> , <b>2016</b> , 94,	3.3	9
98	The growth and characterisation of back-gated high mobility two-dimensional electron gas structures. <i>Journal of Crystal Growth</i> , <b>1991</b> , 111, 300-304	1.6	9
97	Optimal operation points for ultrafast, highly coherent Ge hole spin-orbit qubits. <i>Npj Quantum Information</i> , <b>2021</b> , 7,	8.6	9
96	Spin Control Without Magnetic Fields. <i>Physics Magazine</i> , <b>2016</b> , 9,	1.1	9

95	Spin-orbit coupling in silicon for electrons bound to donors. <i>Npj Quantum Information</i> , <b>2018</b> , 4,	8.6	9
94	g-factor and well-width fluctuations as a function of carrier density in the two-dimensional hole accumulation layer of transfer-doped diamond. <i>Physical Review B</i> , <b>2019</b> , 99,	3.3	8
93	Noncollinear paramagnetism of a GaAs two-dimensional hole system. <i>Physical Review Letters</i> , <b>2014</b> , 113, 236401	7.4	8
92	The 0.7 anomaly in one-dimensional hole quantum wires. <i>Journal of Physics Condensed Matter</i> , <b>2008</b> , 20, 164205	1.8	8
91	Modelling of electrostatic gate operations in the Kane solid state quantum computer. <i>Microelectronics Journal</i> , <b>2002</b> , 33, 1053-1058	1.8	8
90	Theory of hole-spin qubits in strained germanium quantum dots. <i>Physical Review B</i> , <b>2021</b> , 103,	3.3	8
89	Near-Field Excited Archimedean-like Tiling Patterns in Phonon-Polaritonic Crystals. <i>ACS Nano</i> , <b>2021</b> , 15, 9134-9142	16.7	8
88	Experimental conditions for the observation of electron-hole superfluidity in GaAs heterostructures. <i>Physical Review B</i> , <b>2020</b> , 101,	3.3	7
87	Dependence of the 0.7 anomaly on the curvature of the potential barrier in quantum wires. <i>Physical Review B</i> , <b>2015</b> , 91,	3.3	7
86	Hybrid architecture for shallow accumulation mode AlGaAs/GaAs heterostructures with epitaxial gates. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 012105	3.4	7
85	An improved process for fabricating high-mobility organic molecular crystal field-effect transistors. <i>Journal of Applied Physics</i> , <b>2007</b> , 102, 084511	2.5	7
84	The twin radio frequency single electron transistor for correlated charge detection on microsecond time-scales. <i>Microelectronic Engineering</i> , <b>2003</b> , 67-68, 775-781	2.5	7
83	Single atom Si nanoelectronics using controlled single-ion implantation. <i>Microelectronic Engineering</i> , <b>2005</b> , 78-79, 279-286	2.5	7
82	A self-aligned fabrication process for silicon quantum computer devices. <i>Nanotechnology</i> , <b>2002</b> , 13, 686-690	3.4	7
81	The fabrication of back-gated high electron mobility transistors by a novel approach using MBE regrowth on an in situ ion beam patterned epilayer. <i>Journal of Crystal Growth</i> , <b>1993</b> , 127, 41-45	1.6	7
80	Probing the sensitivity of electron wave interference to disorder-induced scattering in solid-state devices. <i>Physical Review B</i> , <b>2012</b> , 85,	3.3	6
79	Integer quantum Hall states in coupled double electron gas systems at mismatched carrier densities. <i>Journal of Physics Condensed Matter</i> , <b>1996</b> , 8, L311-L318	1.8	6
78	Superconductivity in metal-mixed ion-implanted polymer films. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 152503	3.4	6



77	Use of low-temperature Hall effect to measure dopant activation: Role of electron-electron interactions. <i>Physical Review B</i> , <b>2007</b> , 76,	3-3	6
76	Current suppression in a double-island single-electron transistor for detection of degenerate charge configurations of a floating double-dot. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 4640-4642	3-4	6
75	Uranium Superconductivity Redux. <i>Journal of Superconductivity and Novel Magnetism</i> , <b>2000</b> , 13, 833-835		6
74	Using light and heat to controllably switch and reset disorder configuration in nanoscale devices. <i>Physical Review B</i> , <b>2015</b> , 91,	3-3	5
73	Multiband Mechanism for the Sign Reversal of Coulomb Drag Observed in Double Bilayer Graphene Heterostructures. <i>Physical Review Letters</i> , <b>2018</b> , 121, 036601	7-4	5
72	Radio-frequency reflectometry on an undoped AlGaAs/GaAs single electron transistor. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 012114	3-4	5
71	Fabrication and characterisation of gallium arsenide ambipolar quantum point contacts. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 183504	3-4	5
70	Electrometry using the quantum Hall effect in a bilayer two-dimensional electron system. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 212102	3-4	5
69	Overlapping-gate architecture for silicon Hall bar field-effect transistors in the low electron density regime. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 152102	3-4	5
68	Double-island single-electron transistor for noise-suppressed detection of charge transfer. <i>Microelectronic Engineering</i> , <b>2003</b> , 67-68, 826-831	2-5	5
67	Measurements of a composite fermion split-gate. <i>Surface Science</i> , <b>1996</b> , 361-362, 71-74	1-8	5
66	Ultrahigh vacuum in situ fabrication of three-dimensional semiconductor structures using a combination of particle beams. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1992</b> , 10, 2834		5
65	Landau level spin diode in a GaAs two dimensional hole system. <i>New Journal of Physics</i> , <b>2015</b> , 17, 033035	2-9	4
64	Double-layer-gate architecture for few-hole GaAs quantum dots. <i>Nanotechnology</i> , <b>2016</b> , 27, 334001	3-4	4
63	A study of transport suppression in an undoped AlGaAs/GaAs quantum dot single-electron transistor. <i>Journal of Physics Condensed Matter</i> , <b>2013</b> , 25, 505302	1-8	4
62	Anomalous transport in mesoscopic inhomogeneous two-dimensional electron systems at low temperature. <i>Physical Review B</i> , <b>2010</b> , 82,	3-3	4
61	Quantum-dot cellular automata: introduction and experimental overview		4
60	Magnetic susceptibility of the normal-superconducting transition in high-purity single-crystal Uranium. <i>Physical Review B</i> , <b>2002</b> , 66,	3-3	4

59	Probing the band structure of a two-dimensional hole gas using a one-dimensional superlattice. <i>Physical Review B</i> , <b>1996</b> , 54, R14273-R14276	3-3	4
58	Quasi-one-dimensional transport in semiconductor microstructures. <i>Physica Scripta</i> , <b>1992</b> , T45, 200-205	2.6	4
57	Improving reproducibility of quantum devices with completely undoped architectures. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 183101	3-4	4
56	New signatures of the spin gap in quantum point contacts. <i>Nature Communications</i> , <b>2021</b> , 12, 5	17.4	4
55	Signatures of quantum mechanical Zeeman effect in classical transport due to topological properties of two-dimensional spin-3/2 holes. <i>Physical Review B</i> , <b>2020</b> , 101,	3-3	3
54	Origin of the hysteresis in bilayer two-dimensional systems in the quantum Hall regime. <i>Physical Review B</i> , <b>2010</b> , 82,	3-3	3
53	The effect of temperature and gas flow on the physical vapour growth of mm-scale rubrene crystals for organic FETs <b>2007</b> ,		3
52	The fate of quantum Hall extended states as $B \rightarrow 0$ and the possibility of a 2D metal. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2002</b> , 12, 646-649	3	3
51	Scaling of coherent tunneling adiabatic passage in solid-state coherent quantum systems <b>2005</b> ,		3
50	Metallic behaviour and localisation in 2D GaAs hole systems. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2001</b> , 11, 161-166	3	3
49	Single-electron transistor architectures for charge motion detection in solid-state quantum computer devices. <i>Smart Materials and Structures</i> , <b>2002</b> , 11, 749-755	3-4	3
48	Electron-hole superfluidity in strained Si/Ge type II heterojunctions. <i>Npj Quantum Materials</i> , <b>2021</b> , 6,	5	3
47	Lightly strained germanium quantum wells with hole mobility exceeding one million. <i>Applied Physics Letters</i> , <b>2022</b> , 120, 122104	3-4	3
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